Erratum: “Evidence for field enhanced electron capture by EL2 centers in semi-insulating GaAs and the effect on GaAs radiation detectors” [J. Appl. Phys. 75, 7910 (1994)]

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A typographic error appeared in Eq. (5) on page 7911 which should correctly read

\[
N_{DD}^+ \sim \frac{N_{DD}}{1 + n \sigma_n \nu_e/e_n}.
\]

We also gratefully acknowledge the assistance of Dr. David C. Look at Wright State University for bringing to our attention the proper degeneracy factors for the Fermi functions in Eqs. (4), (6), and (7). The degeneracy factors should be represented as 2 instead of 1/2. A degeneracy factor of 1/2 is expected for a single donor level in GaAs. The empty state has degeneracy of \( g_0 = 1 \) and the singly filled state has degeneracy of \( g_1 = 2 \), hence the ratio \( g_0/g_1 = 1/2 \). However, the EL2 deep donor defect is a double donor and the doubly filled state degeneracy is \( g_2 = 1 \). Since we are concerned with the \((0/+)\) state, the degeneracy factors in Eqs. (4), (6), and (7) should be \( g_1/g_2 = 2 \). The change in degeneracy factors does not affect the calculated results and does not compromise the concept or proposed model. However, in order to accurately describe the Fermi functions, we feel we should bring this correction to our readers' attention.

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